

Band switching diode

DAP236U / DAP236K

●Applications

High frequency switching

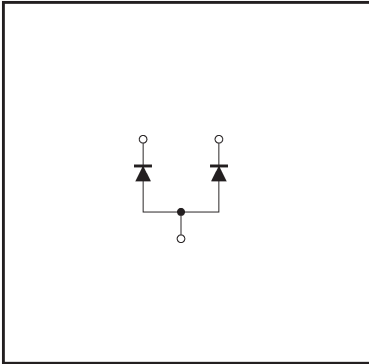
●Features

- 1) Multiple diodes with common anode configuration.
- 2) High reliability.

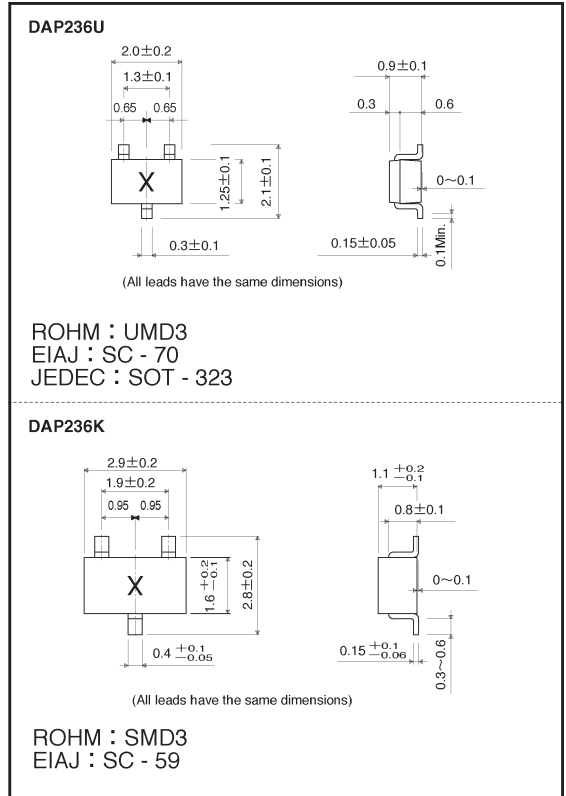
●Construction

Silicon epitaxial planar

●Equivalent circuit



●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V _R	35	V
Power dissipation	P _d	150	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55~+125	°C

●Electrical characteristics (Ta = 25°C unless specified otherwise)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.87	1.0	V	$I_F=10\text{mA}$
Reverse current	I_R	—	0.01	10	nA	$V_R=25\text{V}$
Capacitance between terminals	C_T	—	0.80	1.2	pF	$V_R=6\text{V}$, $f=1\text{MHz}$
Forward operating resistance	r_F	—	0.60	0.90	Ω	$I_F=2\text{mA}$, $f=100\text{MHz}$

●Electrical characteristic curves (Ta = 25°C)

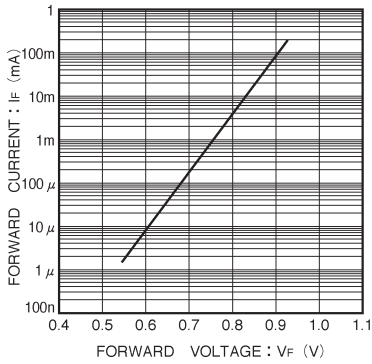


Fig. 1 Forward characteristics

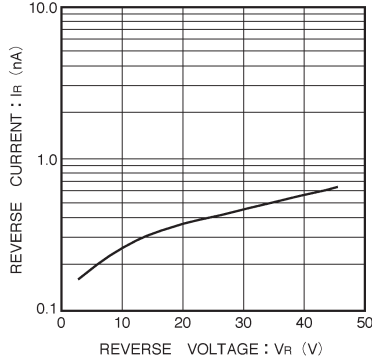


Fig. 2 Reverse characteristics

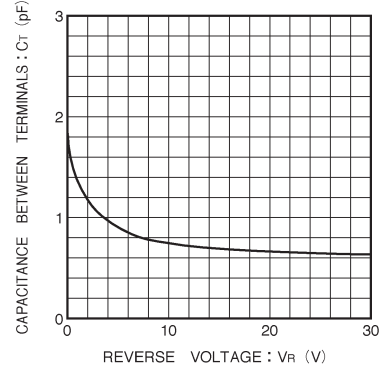


Fig. 3 Capacitance between terminals characteristics

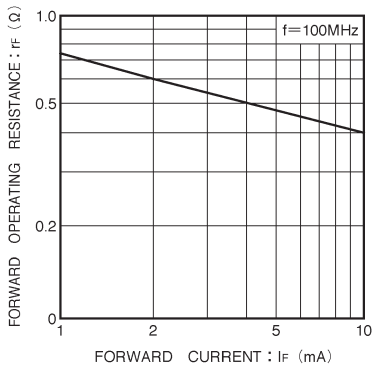


Fig. 4 Forward operating resistance characteristics

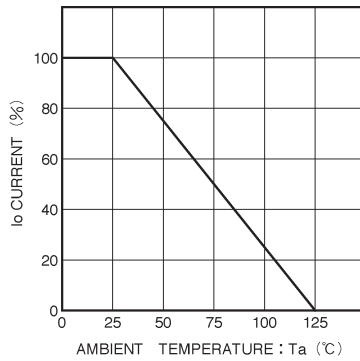


Fig. 5 Derating curve (mounting on glass epoxy PCBs)